Silicon NPN Power Transistors 2SC2827

DESCRIPTION

- With TO-220C package
- High breakdown voltage
- Fast switching speed.
- Wide area of safe operation

APPLICATIONS

- 400V/7A switching regulator applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

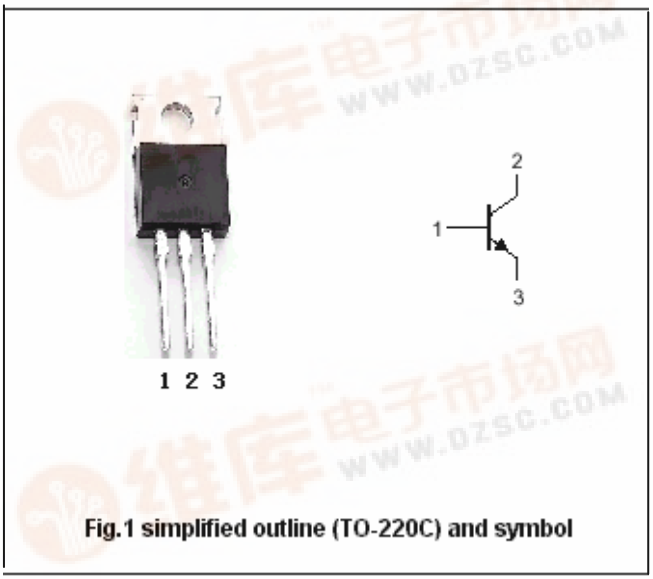

Fig.1 simplified outline (TO-220C) and symbol

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	450	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		6	A
P_C	Collector dissipation	T_C=25℃	50	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=10mA ; I_B=0	450			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ; I_C=0	6			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_C=4A; I_B=0.8A			1.0	V
$V_{BE(sat)}$	Base-emitter saturation voltage	I_C=4A; I_B=0.8A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=500V ;I_E=0			100	μA
I_{CEO}	Collector cut-off current	V_{CE}=450V ; I_B=0			100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			100	μA
h_{FE}	DC current gain	I_C=3A ; V_{CE}=2V	10			
f_T	Transition frequency	I_C=0.5A ; V_{CE}=10V		20		MHz

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PACKAGE OUTLINE

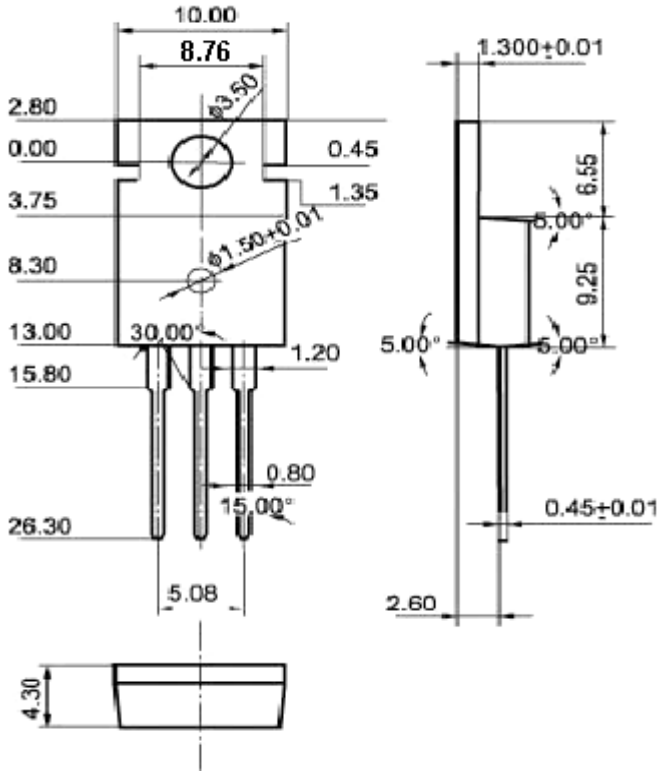

Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)